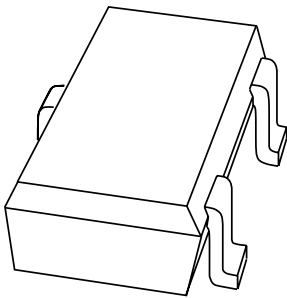


DATA SHEET



BAV199W

Low-leakage double diode

Product data sheet
Supersedes data of 1998 Jan 09

1999 May 11

Low-leakage double diode

BAV199W

FEATURES

- Small plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

- Low-leakage current applications in surface mounted circuits.

DESCRIPTION

Epitaxial, medium-speed switching, double diode in a small plastic SOT323 (SC-70) SMD package. The diodes are connected in series.

PINNING

PIN	DESCRIPTION
1	anode
2	cathode
3	cathode; anode

Top view

MAM391

Marking code: JY- = made in Hong Kong; JYt = made in Malaysia.

Fig.1 Simplified outline (SOT323; SC-70) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode unless otherwise specified					
V _R	continuous reverse voltage		–	75	V
V _{RRM}	repetitive peak reverse voltage		–	85	V
I _F	continuous forward current	single diode loaded; T _s = 90 °C; see Fig.2	–	135	mA
		double diode loaded; T _s = 90 °C; see Fig.2	–	110	mA
I _{FRM}	repetitive peak forward current		–	500	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t _p = 1 μs	–	4	A
		t _p = 1 ms	–	1	A
		t _p = 1 s	–	0.5	A
P _{tot}	total power dissipation	single diode loaded; T _s = 90 °C	–	150	mW
		double diode loaded; T _s = 90 °C	–	240	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C

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ELECTRICAL CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					
V_F	forward voltage	see Fig.3			
		$I_F = 1\text{ mA}$	–	900	mV
		$I_F = 10\text{ mA}$	–	1000	mV
		$I_F = 50\text{ mA}$	–	1100	mV
		$I_F = 150\text{ mA}$	–	1250	mV
I_R	reverse current	see Fig.5			
		$V_R = 75\text{ V}$	0.003	5	nA
		$V_R = 75\text{ V}; T_j = 150\text{ °C}$	3	80	nA
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0$; see Fig.6	2	–	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\ \Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7	0.8	3	μs

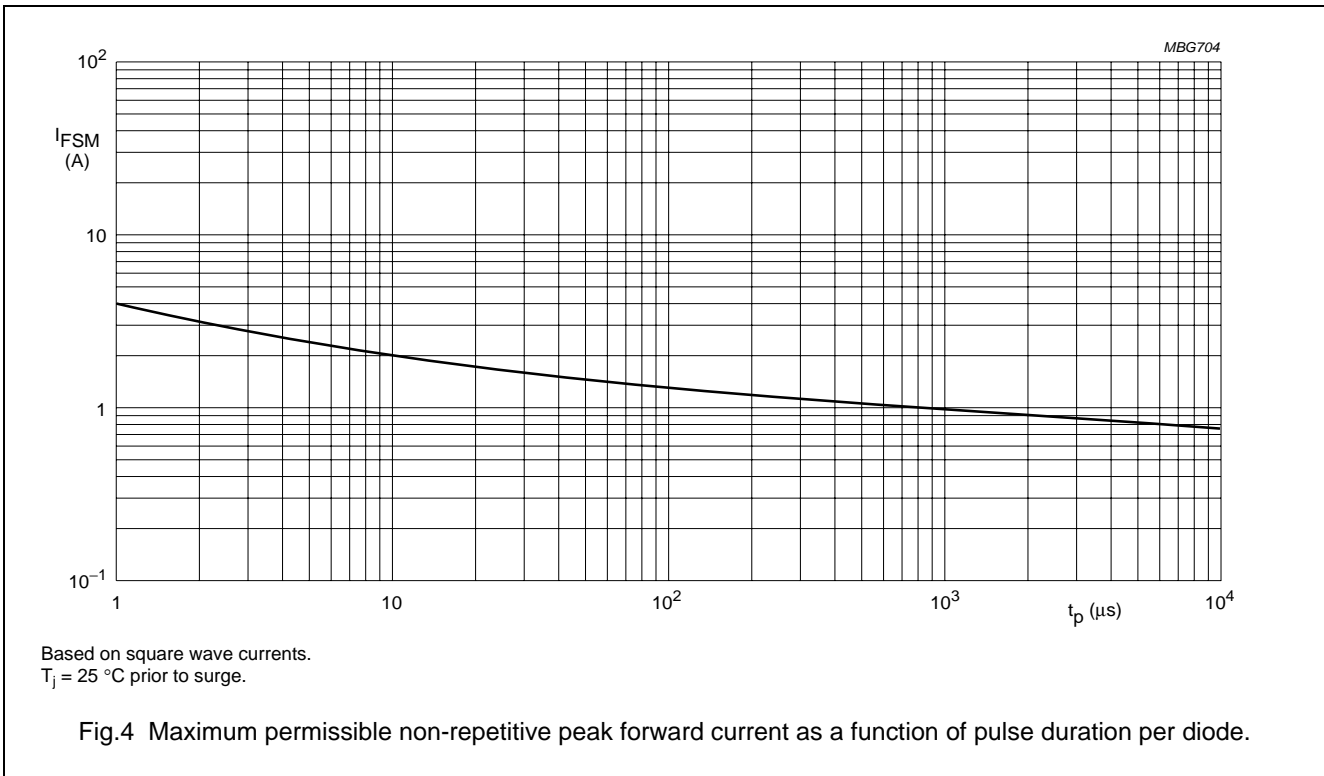
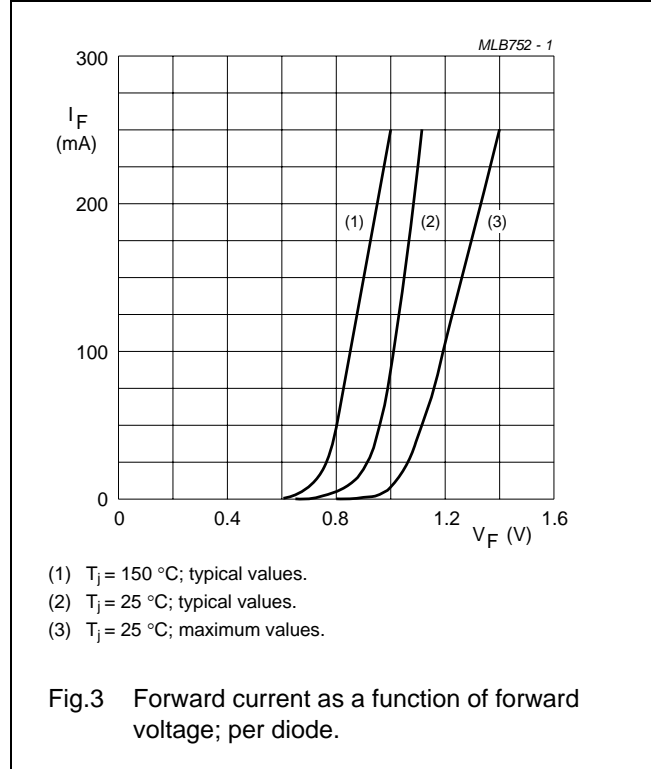
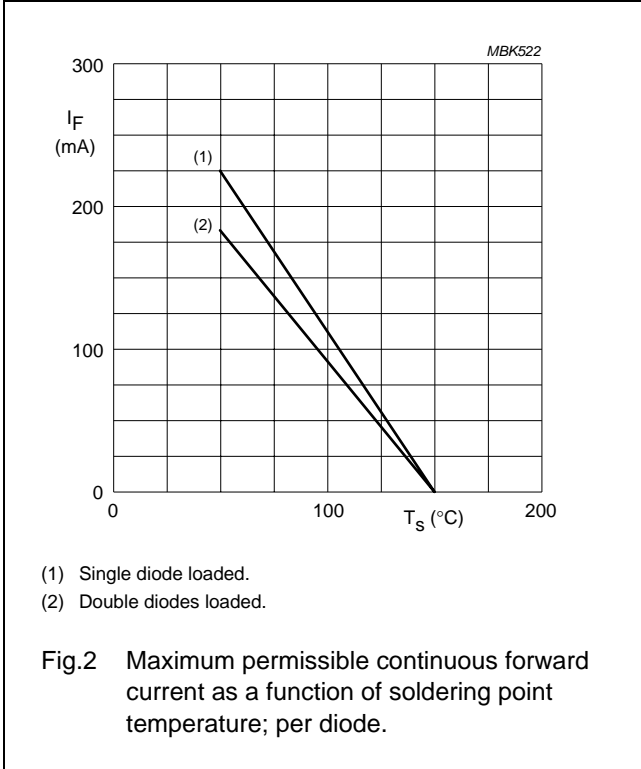
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	$T_s = 90\text{ °C}$	400	K/W

Low-leakage double diode

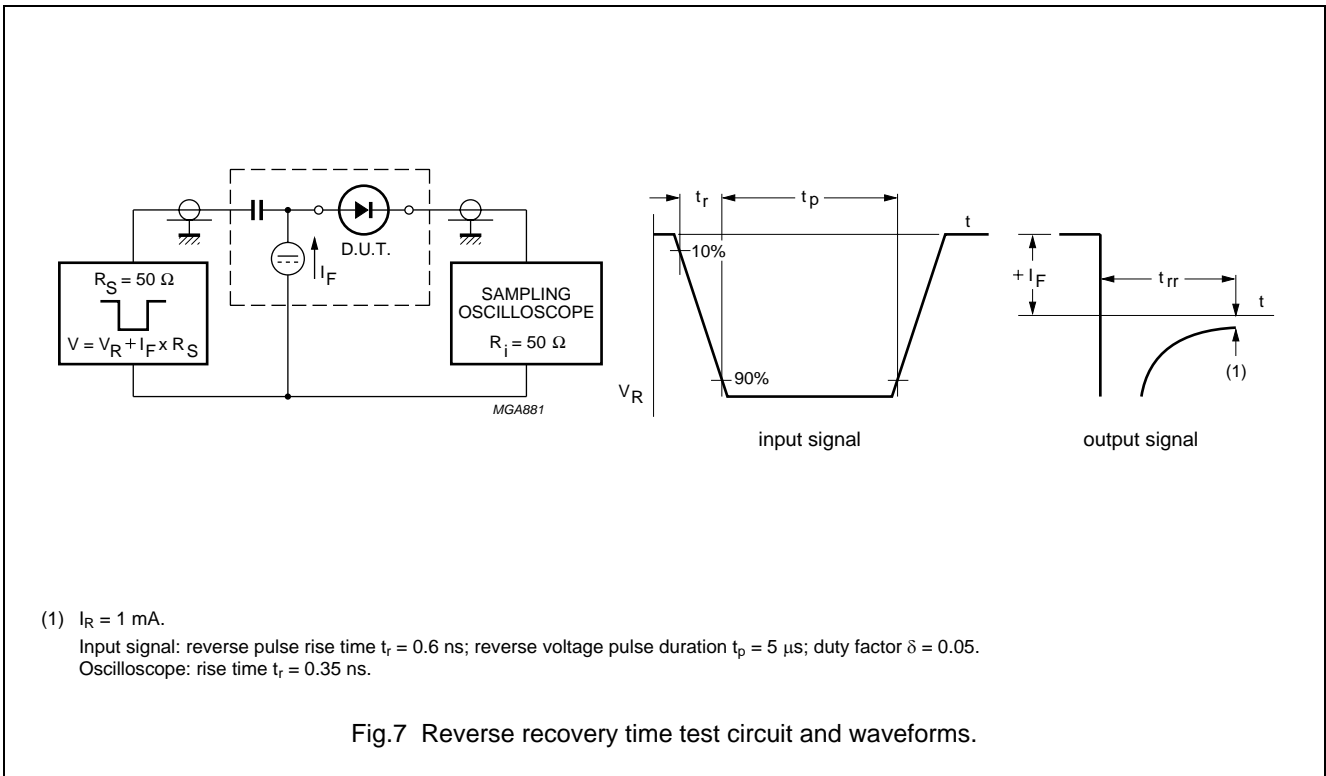
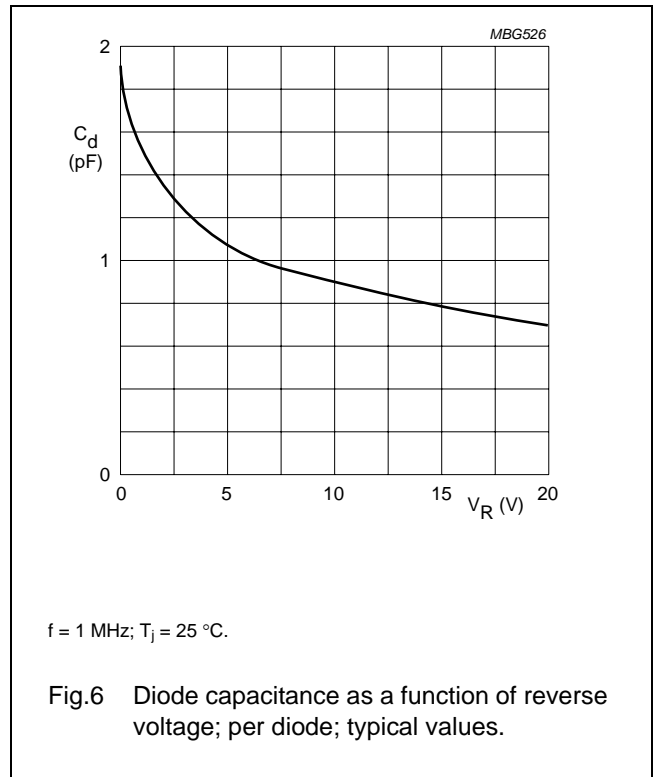
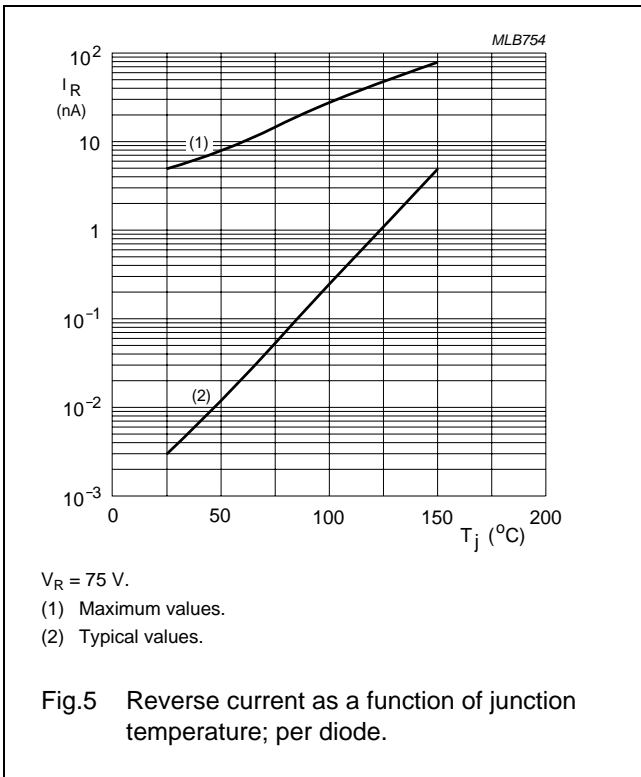
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GRAPHICAL DATA



Low-leakage double diode

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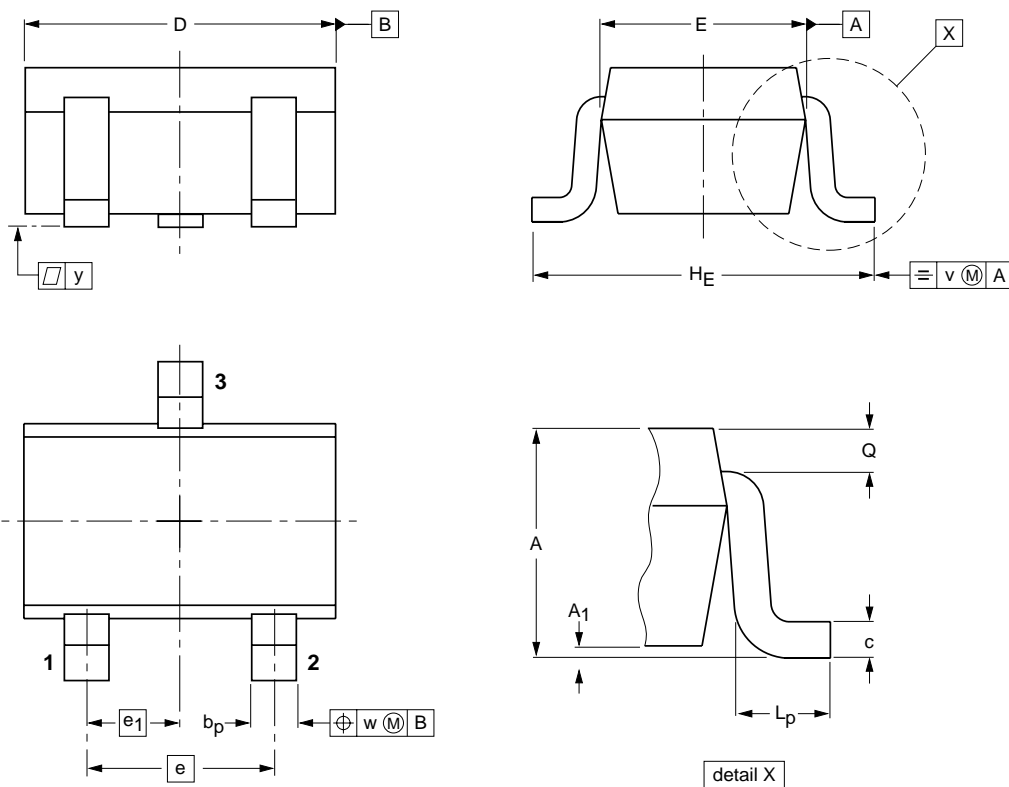
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT323			SC-70		97-02-28

Low-leakage double diode

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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